



ON Semiconductor®

FDN360P

Single P-Channel, PowerTrench[®] MOSFET

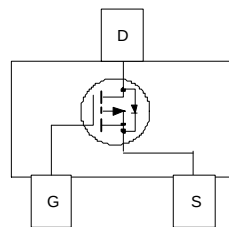
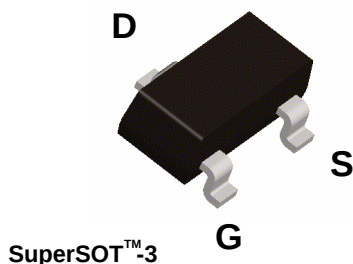
General Description

This P-Channel Logic Level MOSFET is produced using ON Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- -2 A, -30 V. $R_{DS(ON)} = 80\text{ m}\Omega$ @ $V_{GS} = -10\text{ V}$
 $R_{DS(ON)} = 125\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
- Low gate charge (6.2 nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$.
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.
- These Devices are Pb-Free and are RoHS Compliant



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	-2	A
	– Pulsed	-10	
P_D	Power Dissipation for Single Operation (Note 1a)	0.5	W
	(Note 1b)	0.46	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
360	FDN360P	7"	8mm	3000 units

Electrical Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units	
Off Characteristics							
BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _D = –250 μA	–30			V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = –250 μA, Referenced to 25°C		–22		mV/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = –24V, V _{GS} = 0 V			–1	μA	
		V _{DS} = –24V, V _{GS} = 0 V, T _J =55°C			–10		
I _{GSSF}	Gate–Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA	
I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = –20 V, V _{DS} = 0 V			–100	nA	
On Characteristics (Note 2)							
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = –250 μA	–1	–1.9	–3	V	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = –250 μA, Referenced to 25°C		4		mV/°C	
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = –10 V, I _D = –2 A V _{GS} = –10 V, I _D = –2 A, T _J =125°C V _{GS} = –4.5 V, I _D = –1.5A		63 90 100	80 136 125	mΩ	
I _{D(on)}	On–State Drain Current	V _{GS} = –10 V, V _{DS} = –5 V	–10			A	
g _{FS}	Forward Transconductance	V _{DS} = –5 V, I _D = –2 A		5		S	
Dynamic Characteristics							
C _{iss}	Input Capacitance	V _{DS} = –15 V, V _{GS} = 0 V, f = 1.0 MHz		298		pF	
C _{oss}	Output Capacitance				83		pF
C _{rss}	Reverse Transfer Capacitance				39		pF
Switching Characteristics (Note 2)							
t _{d(on)}	Turn–On Delay Time	V _{DD} = –15 V, I _D = –1 A, V _{GS} = –10 V, R _{GEN} = 6 Ω		6	12	ns	
t _r	Turn–On Rise Time			13	23	ns	
t _{d(off)}	Turn–Off Delay Time			11	20	ns	
t _f	Turn–Off Fall Time			6	12	ns	
Q _g	Total Gate Charge	V _{DS} = –15V, I _D = –3.6 A, V _{GS} = –10 V		6.2	9	nC	
Q _{gs}	Gate–Source Charge			1		nC	
Q _{gd}	Gate–Drain Charge			1.2		nC	
Drain–Source Diode Characteristics and Maximum Ratings							
I _S	Maximum Continuous Drain–Source Diode Forward Current				–0.42	A	
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = –0.42 A (Note 2)		–0.8	–1.2	V	

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in^2 pad of 2 oz. copper.



b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

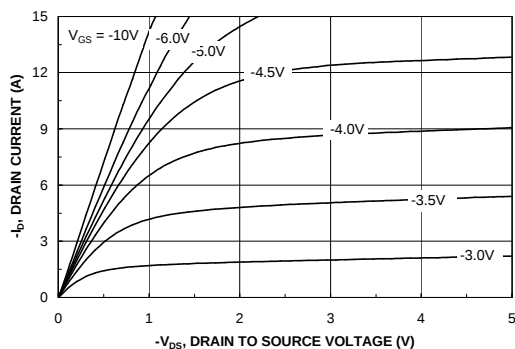


Figure 1. On-Region Characteristics.

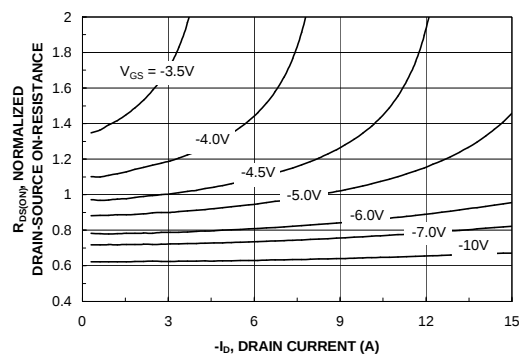


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

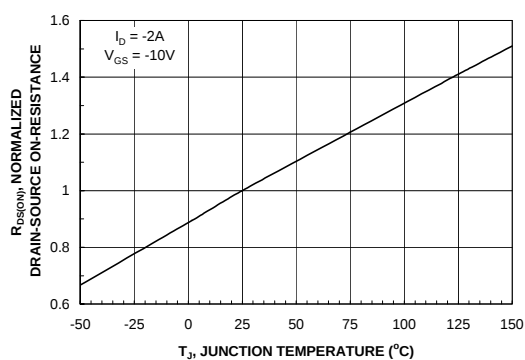


Figure 3. On-Resistance Variation with Temperature.

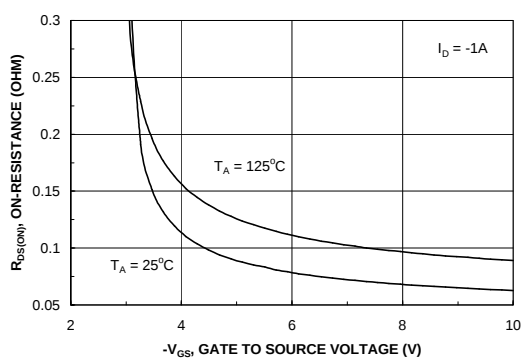


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

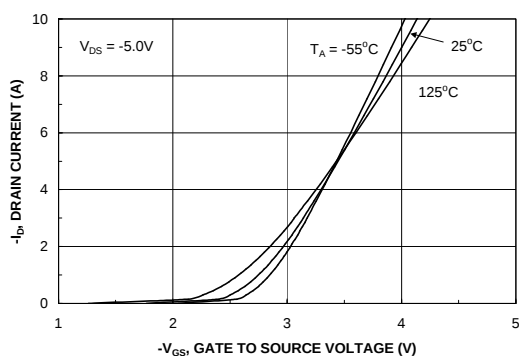


Figure 5. Transfer Characteristics.

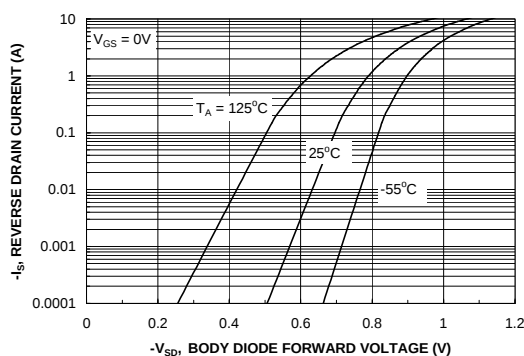


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

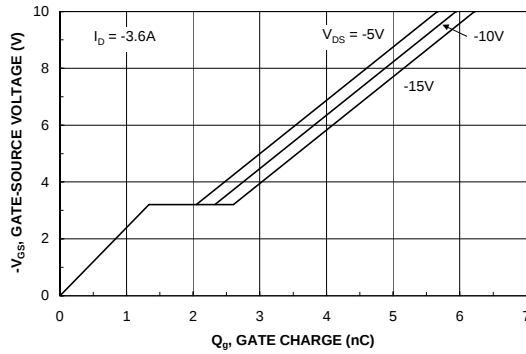


Figure 7. Gate Charge Characteristics.

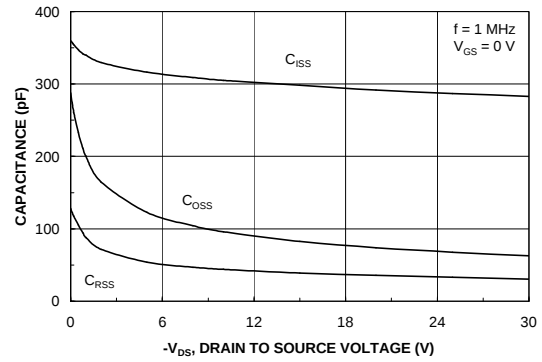


Figure 8. Capacitance Characteristics.

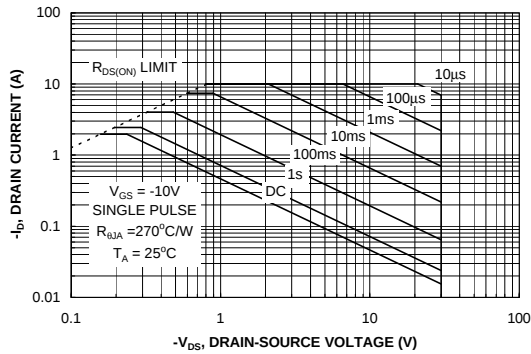


Figure 9. Maximum Safe Operating Area.

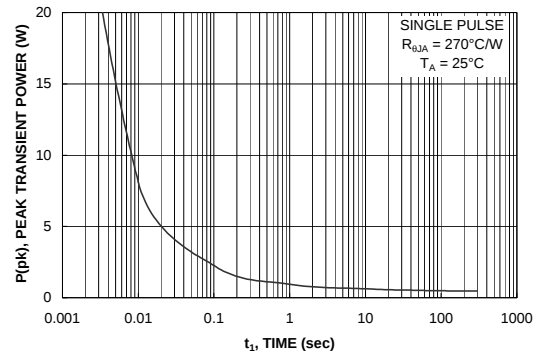


Figure 10. Single Pulse Maximum Power Dissipation.

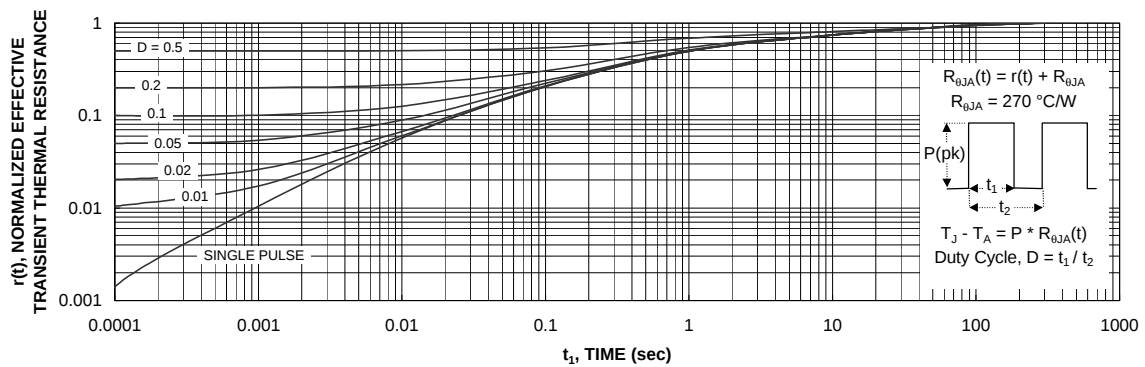


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

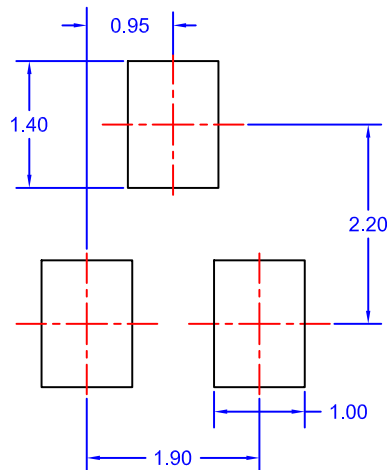
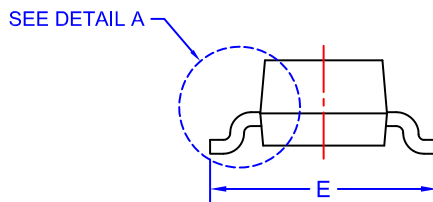
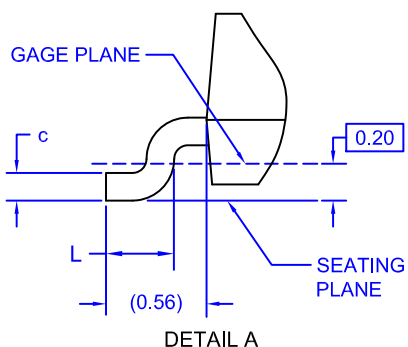
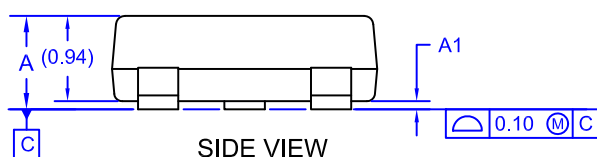
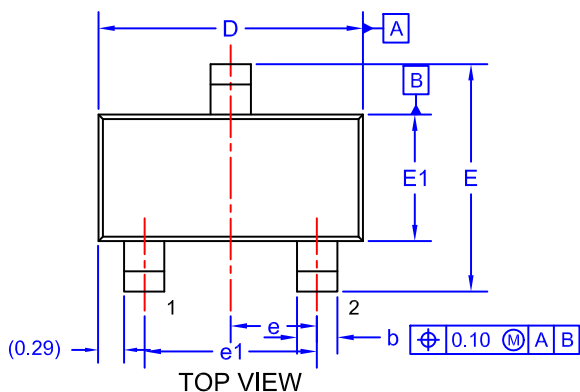


SOT-23/SUPERSOT™ –23, 3 LEAD, 1.4x2.9

CASE 527AG

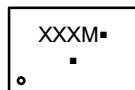
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*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-23/SUPERSOT-23, 3 LEAD, 1.4X2.9	PAGE 1 OF 1

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